Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	1653	(372/46.01).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/15 11:48
S3	240	S2 nitride @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 11:50
S4	2315	laser substrate (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:25
S5	797	laser (substrate with GaN) (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:26
S6	344	laser (substrate with GaN) (substrate with doped) (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:48
S14	0	laser (substrate with GaN) (substrate with O-doped) (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:48
S15	6	laser (substrate with GaN) (substrate with O with doped) (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:48
S16	11	laser (substrate with GaN) (substrate with doped with oxygen) (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:54

S17	16	laser (substrate with GaN) (substrate with doped with (O or oxygen)) (guide$3 or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 16:55
S18	16	laser (substrate with GaN) (substrate with doped with (O or oxygen)) (guide or confinement or waveguide) (nitride or boride) cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 09:15
S19	198	laser (substrate with GaN) (substrate with doped with (O or Si)) ((guide or confinement or waveguide)or (light guide)) nitride cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 17:36
S20	143	laser (substrate with GaN) (substrate with doped with (O or Si)) (light guide) nitride cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 17:37
S21	28	laser (substrate with GaN) (substrate with doped with (O or Si)) "light guide" nitride cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 17:44
S22	90	laser (substrate with GaN) (substrate with doped with (O or Si)) ("light guide" or "second cladding") nitride cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 17:53
S23	6	(substrate with GaN) (substrate with doped with (O or Si)) ("light guide" or "second cladding") nitride cladding "carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/16 09:56
S24	95521	only one light guide layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/15 17:56

S25	2225	only one light guide layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2005/08/16 17:51
S26	69	only one light guide layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2005/08/15 17:58
S27	31	(only one light guide layer) and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2005/08/15 17:59
S28	6	(substrate with (AlN or GaN)) (substrate with doped with (O or Si)) ("light guide" or "second cladding") nitride cladding "carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/16 09:58
S29	13	(substrate with (AlN or GaN)) (substrate with doped with (O or Si)) ("light guide" or "second cladding" or confinement or waveguide) nitride cladding "carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/16 10:09
S30	46	(substrate with (AlN or GaN)) (substrate with doped with (O or Si)) ("light guide" or "second cladding" or confinement or waveguide) nitride cladding ("carrier blocking" or "current blocking")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/16 10:10
S31	2	"only one light guide layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2005/08/16 17:52
S32	3	("6110756" | "6285697" | "6411637").PN. OR ("6803596"). URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/08/16 18:03
S34	16	laser (substrate with GaN) (substrate with doped with (O or oxygen)) (guide or confinement or waveguide) nitride cladding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 09:15

S35	5	laser (substrate with GaN) (substrate with doped with (O or oxygen)) (guide or confinement or waveguide) nitride cladding "carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 09:17
S36	5	(substrate with GaN) (substrate with doped with (O or oxygen)) (guide or confinement or waveguide) nitride cladding "carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 09:20
S37	2	(substrate with (AlN or GaN)) (substrate with doped with (O or oxygen)) (guide or confinement or waveguide) nitride cladding "n-type carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 14:37
S42	2	(substrate with GaN) (substrate with doped with (O or oxygen)) nitride cladding "n-type carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 14:47
S43	2	(substrate with GaN) (substrate with doped with (O or oxygen)) nitride cladding "n-type carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 14:49
S44	2	(substrate with GaN) (substrate with doped with (O or oxygen)) "n-type carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 14:49
S45	6	(substrate with GaN) (substrate with doped with (O or oxygen)) nitride cladding "carrier blocking"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 14:52
S46	0	(substrate with GaN) (substrate with doped with (O or oxygen)) nitride cladding "current blocking" @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 14:53

S47	4	(substrate with GaN) (substrate with doped with (O or oxygen)) nitride cladding @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 15:02
S48	2	(substrate with GaN with doped with (O or oxygen)) nitride cladding @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 15:03
S49	25	(substrate with GaN with doped with (O or oxygen)) @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 15:03
S50	3345	"ion implantation" impurity carbon @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:20
S51	1531	"ion implantation" impurity carbon laser @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:21
S52	26	"ion implantation" impurity carbon laser "current blocking" @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:23
S53	8	"ion implantation" (impurity with carbon) laser "current blocking" @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:25
S54	8	"ion implantation" (impurit$ with carbon) laser "current blocking" @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:27

S55	1	("ion implantation" with "current blocking") (impurit$ with carbon) laser @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:33
S56	1	("ion implantation" with "current blocking") (impurit$ with carbon) @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:51
S57	1	("ion implantation" with ("current blocking" or "current-blocking")) (impurit$ with carbon) @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/17 19:52